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| 1. Ms. Diana Bates U.S. Patent and Trademark Office | (703) 305-7687 | () |
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Cover Sheet Message:

Dear Ms. Bates:

Enclosed is a copy of the signature page of the amendment filed on July 6, 2001 in the captioned application. Thank you for your attention to this matter.

Yours truly,

Frederick A. Spaeth
Registration No. 33,793

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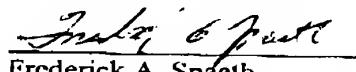
not impede the plasma generated from the silicon bridge from igniting the energetic material. For this reason, by employing titanium in place of tungsten, the resulting invention provides an advantage not recognized in the cited references, i.e., the claimed device will initiate the reactive material much more reliably than prior art devices. It will be understood by one of ordinary skill in the art, upon a reading and understanding of the captioned application, that this advantage could be realized by employing any metal having a melting temperature well below the vaporization temperature of the semiconductor material. For this reason, claims 21, 22 and 23 need not be limited to titanium.

New dependent claim 22 adds further detail to claim 21, specifically defining a procedure which makes use of the relative melting and vaporizing temperatures of titanium and a typical semiconductor material such as silicon.

New dependent claim 23 specifies the use of a metal that is reactive with oxygen to provide the advantage described in the application at page 4, lines 21-28, i.e., that the reaction with oxygen contributes thermal energy towards vaporizing the semiconductor bridge and so reduces the energy requirement for the electrical firing signal. It would be understood by one of ordinary skill in the art, upon a reading and understanding of the captioned application, that this benefit can be attained by the use of oxygen-reactive metals other than titanium.

The stated rejection has been traversed by the foregoing amendments and remarks. Re-examination of the application is respectfully requested.

Respectfully submitted,


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